Low-Voltage CMOS Octal Buffer

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX244 is a high performance, non–inverting octal buffer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V $_{\rm I}$ specification of 5.5 V allows MC74LCX244 inputs to be safely driven from 5 V devices. The MC74LCX244 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable (\overline{OE}) input, when HIGH, disables the output by placing them in a HIGH Z condition.

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V

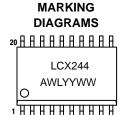


ON Semiconductor™

http://onsemi.com

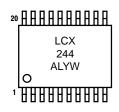


SO-20 DW SUFFIX CASE 751D



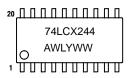


TSSOP-20 DT SUFFIX CASE 948E





CASE 967



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LCX244DW	SO-20	38 Units/Rail
MC74LCX244DWR2	SO-20	1000 Units/Reel
MC74LCX244DT	TSSOP-20	75 Units/Rail
MC74LCX244DTEL	TSSOP-20	2000 Units/Reel
MC74LCX244DTR2	TSSOP-20	2500 Units/Reel
MC74LCX244M	SO EIAJ–20	40 Units/Rail
MC74LCX244MEL	SO EIAJ-20	2000 Units/Reel

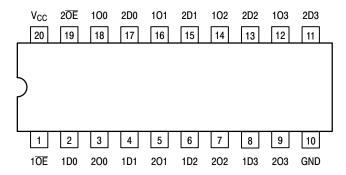
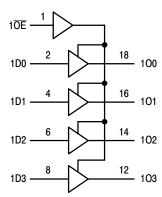


Figure 1. Pinout: 20-Lead (Top View)



PIN NAMES

PINS	FUNCTION
n OE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
10n, 20n	3–State Outputs

TRUTH TABLE

INPUTS		OUTPUTS
1 <u>0E</u> 2 <u>0E</u>	1Dn 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	Х	Z

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

X = High or Low Voltage Level and Transitions are Acceptable For I_{CC} reasons, DO NOT FLOAT Inputs

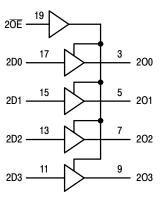


Figure 2. Logic Diagram

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1.)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
V _O	Output Voltage	(HIGH or LOW State) (3–State)	0 0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current	V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			-24 -12	mA
I _{OL}	LOW Level Output Current	V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			24 12	mA
T _A	Operating Free–Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{II} $V_{CC} = 3.0V$	N from 0.8V to 2.0V,	0		10	ns/V

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2.)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		
V _{IL}	LOW Level Input Voltage (Note 2.)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V _{CC} – 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		$V_{CC} = 2.7 \text{ V}; I_{OL} = 12 \text{ mA}$		0.4]
		$V_{CC} = 3.0 \text{ V; } I_{OL} = 16 \text{ mA}$		0.4]
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
I _I	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ
I _{OZ}	3-State Output Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; 0V \le V_{O} \le 5.5 \text{ V};$ $V_{I} = V_{IH} \text{ or V }_{IL}$		±5	μА
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0 \text{ V}; V_{I} \text{ or } V_{O} = 5.5 \text{ V}$		10	μΑ
I _{CC}	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_{I} are used to test DC electrical characteristics only.

AC CHARACTERISTICS ($t_R = t_F = 2.5 \text{ ns}; R_L = 500 \ \Omega$)

					Lim	nits			
					T _A = -40°C to +85°C				
			V _{CC} = 3.0	V to 3.6 V	V _{CC} =	2.7 V	V _{CC} = 2.	5 V ±0.2	
			C _L =	50 pF	C _L = 9	50 pF	C _L = 3	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH}	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	1.5 1.5	7.8 7.8	ns
t _{PZH}	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	10 10	ns
t _{PHZ}	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	8.4 8.4	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3.)			1.0 1.0					ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

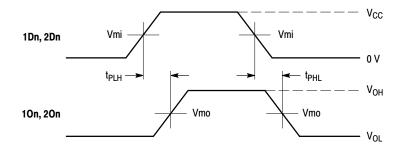
DYNAMIC SWITCHING CHARACTERISTICS

			T,	_A = +25°(
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4.)	$\begin{aligned} & V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ & V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		0.8 0.6		٧
V _{OLV}	Dynamic LOW Valley Voltage (Note 4.)	$\begin{aligned} & V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ & V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V

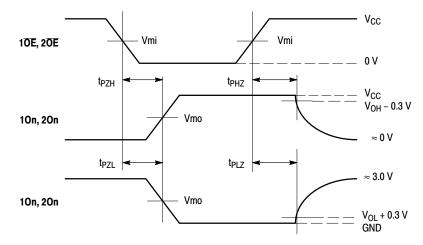
^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	7	рF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	8	рF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



 $\label{eq:waveform 1 - PROPAGATION DELAYS} t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

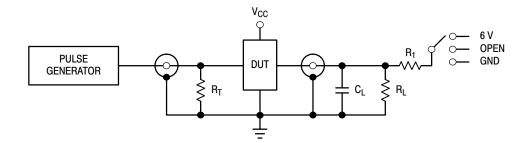


WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Figure 3. AC Waveforms

	Vcc			
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V	
Vmi	1.5 V	1.5 V	V _{CC} /2	
Vmo	1.5 V	1.5 V	V _{CC} /2	
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V	
V_{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V	



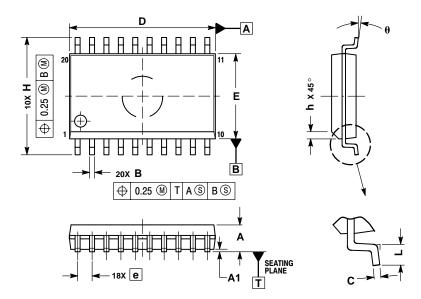
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at V _{CC} = 3.3 ± 0.3 V 6 V at V _{CC} = 2.5 ± 0.2 V
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

 C_L = 50 pF at V_{CC} = 3.3 \pm 0.3 V or equivalent (includes jig and probe capacitance) C_L = 30 pF at V_{CC} = 2.5 \pm 0.2 V or equivalent (includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F

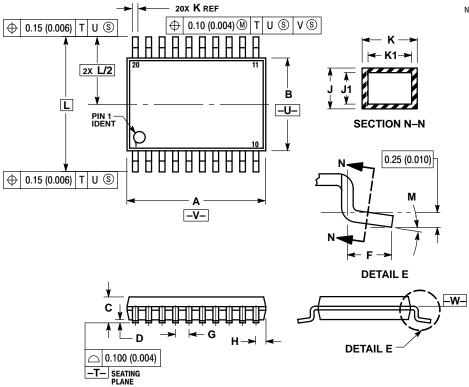


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50 0.90				
θ	0°	7 °			

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 ISSUE A



NOTES:

- JTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

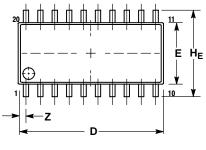
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED
- FLASH OR GATE BURRS SHALL NOT EXCEED
 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT
 EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
- REFERENCE ONLY.

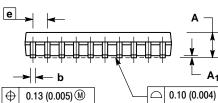
 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

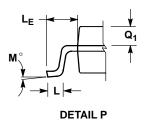
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

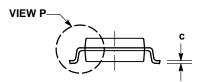
PACKAGE DIMENSIONS

SO EIAJ-20 **M SUFFIX** CASE 967-01 ISSUE O









NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Ε	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.81		0.032

Notes

are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes ON Semiconductor and without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)

Email: ONlit-german@hibbertco.com

Phone: (+1) 303–308–7141 (Mon–Fri 2:00pm to 7:00pm CET)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

Toll-Free from Mexico: Dial 01-800-288-2872 for Access -

then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor - Asia Support

Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031

Phone: 81-3-5740-2700

Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.